



SANYO Semiconductors

## DATA SHEET

# MCH6429

N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±12	V
Drain Current (DC)	I <sub>D</sub>		6	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	24	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	3.8	6.4		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =3A, V <sub>GS</sub> =4V		21	28	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1.5A, V <sub>GS</sub> =2.5V		27	38	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =1.8V		38	76	mΩ

Marking : ZD

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**SANYO Semiconductor Co., Ltd.**

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# MCH6429

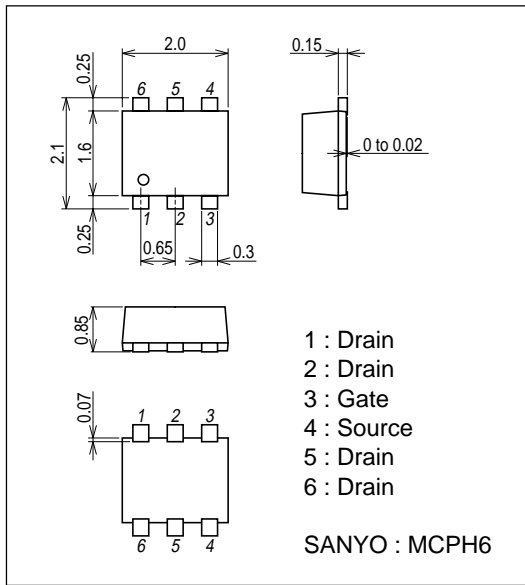
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		680		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		175		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		135		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		13		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		90		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		57		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		91		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =6A		8.2		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =6A		1.45		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =6A		2.7		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =6A, V <sub>GS</sub> =0V		0.8	1.2	V

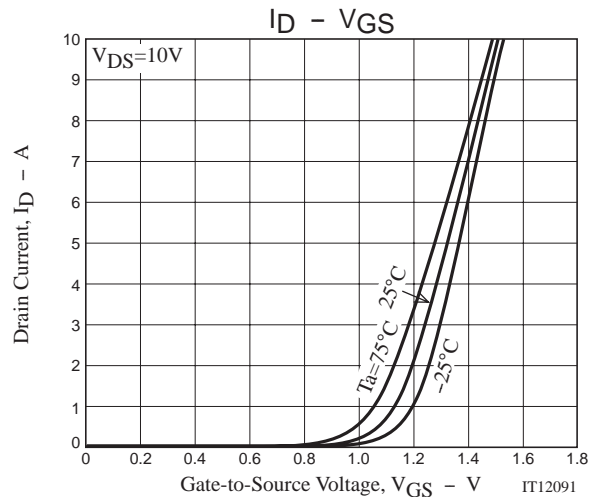
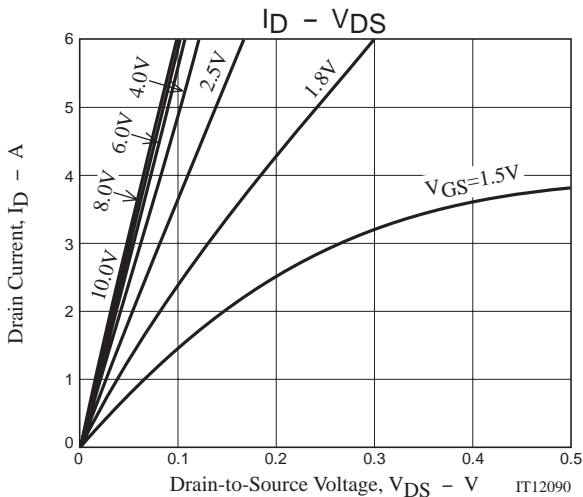
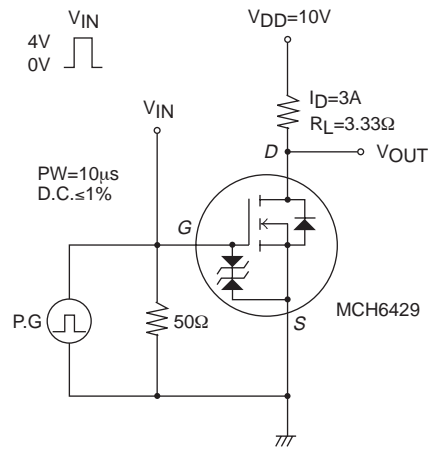
## Package Dimensions

unit : mm (typ)

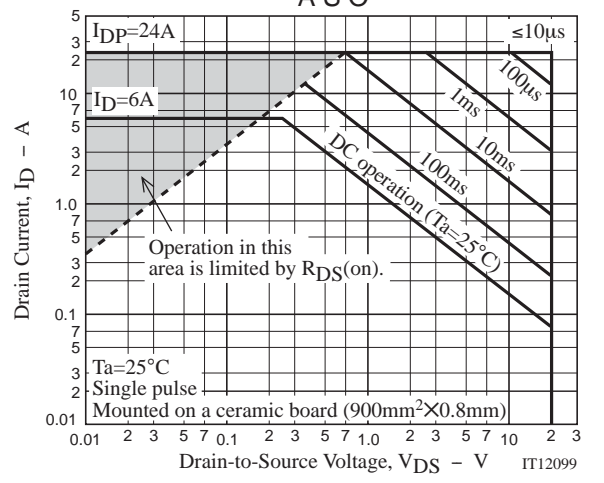
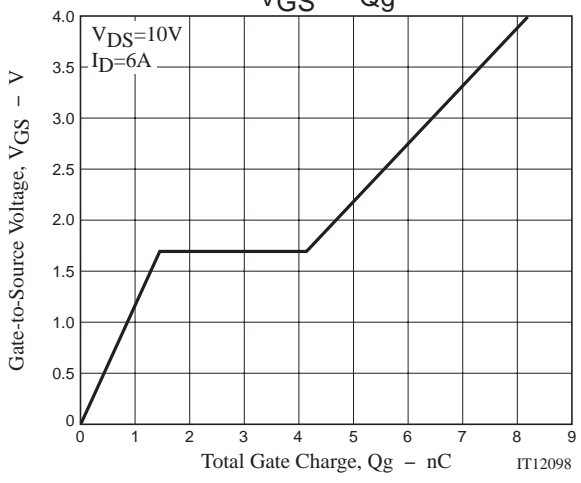
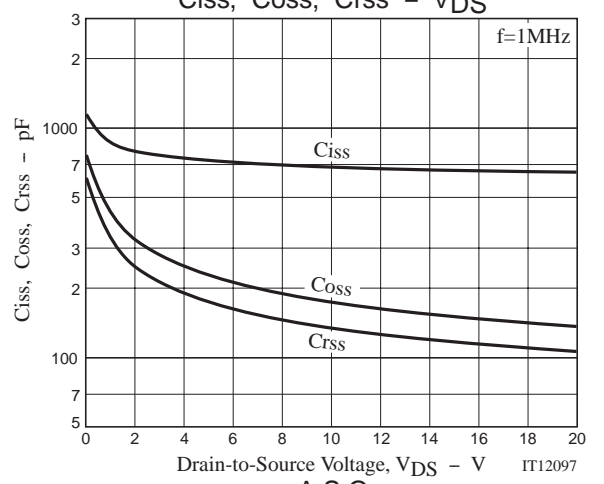
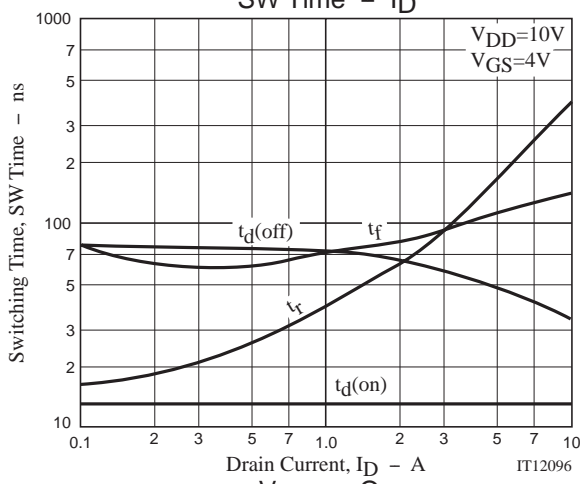
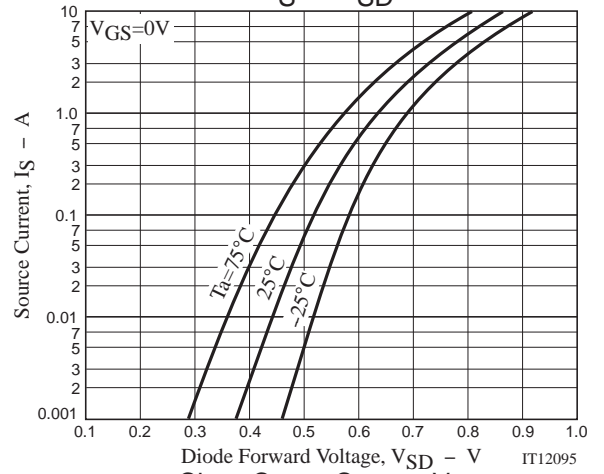
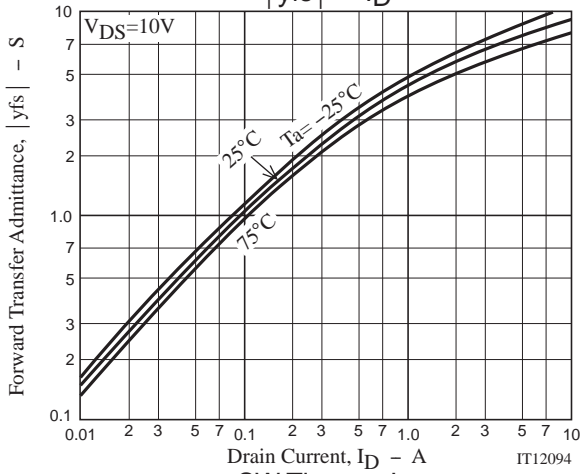
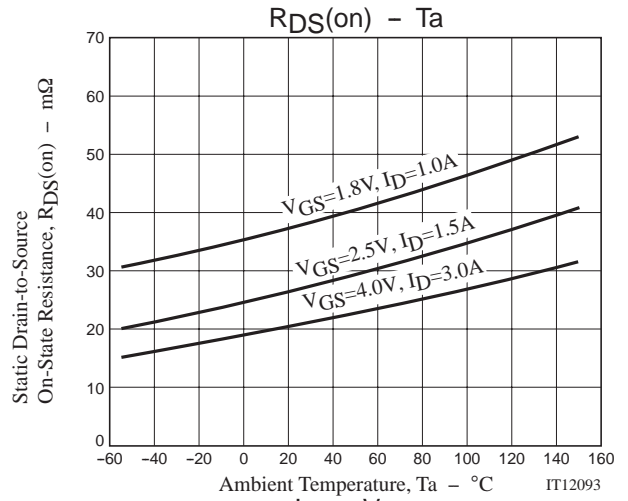
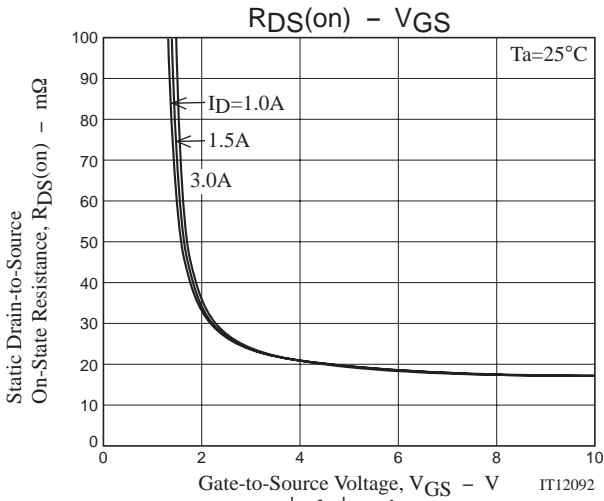
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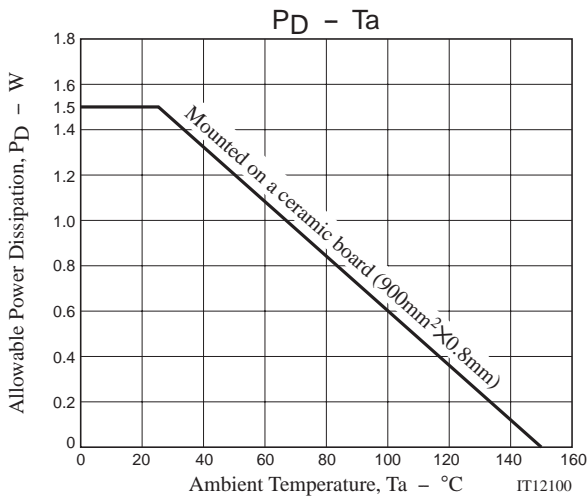


## Switching Time Test Circuit



# MCH6429





Note on usage : Since the MCH6429 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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